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Fabrication and Characterization of Layered Transition Metal Dichalcogenides

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Research Goal

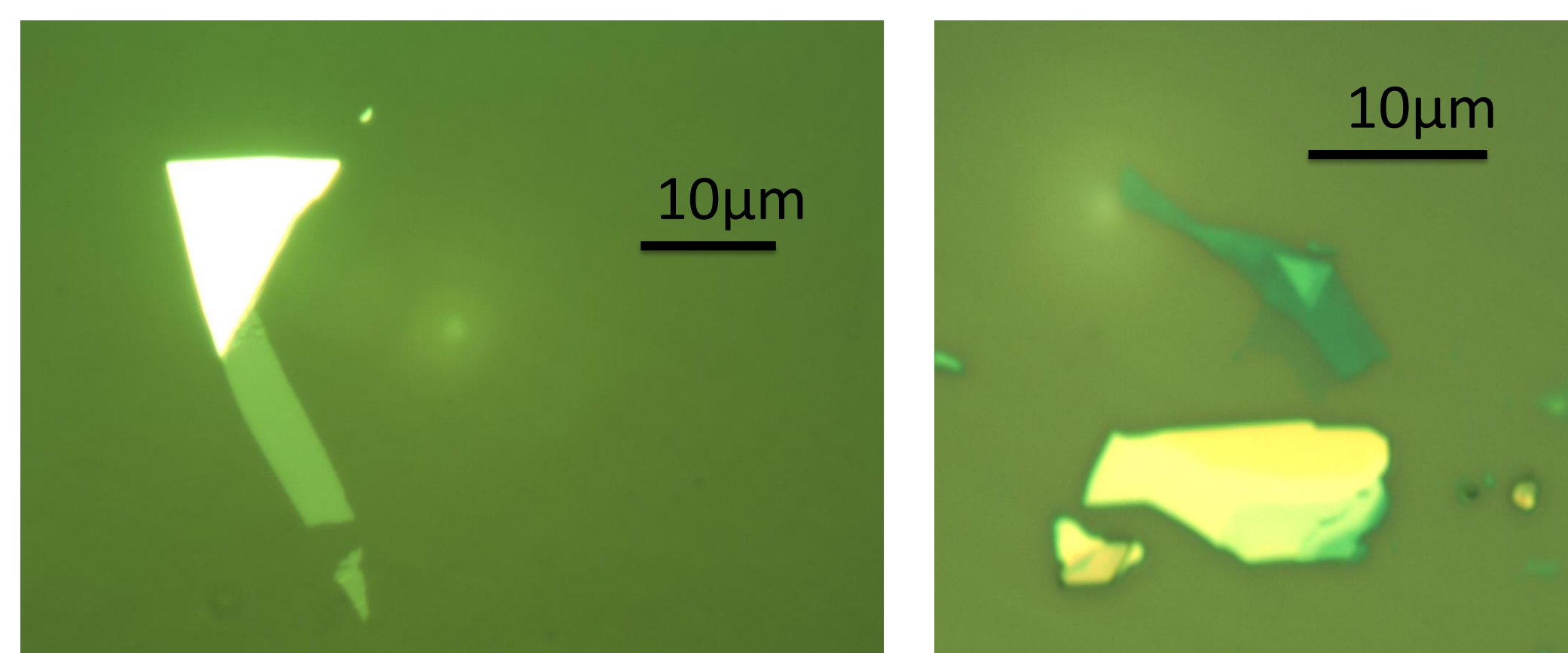
The goal of my research was to mechanically exfoliate single to few atomic layer samples of Molybdenum Disulfide (MoS_2), Tungsten Diselenide (WSe_2), and Tungsten Disulfide (WS_2) and characterize these 2D materials by multiple methods. I used Atomic Force Microscopy, Raman Spectroscopy, and Optical Microscopy to accomplish this. In addition, I measured the electrical properties of the exfoliated materials by fabricating a device and taking basic measurements.

Material Preparation

Mechanical Exfoliation – Scotch Tape Method

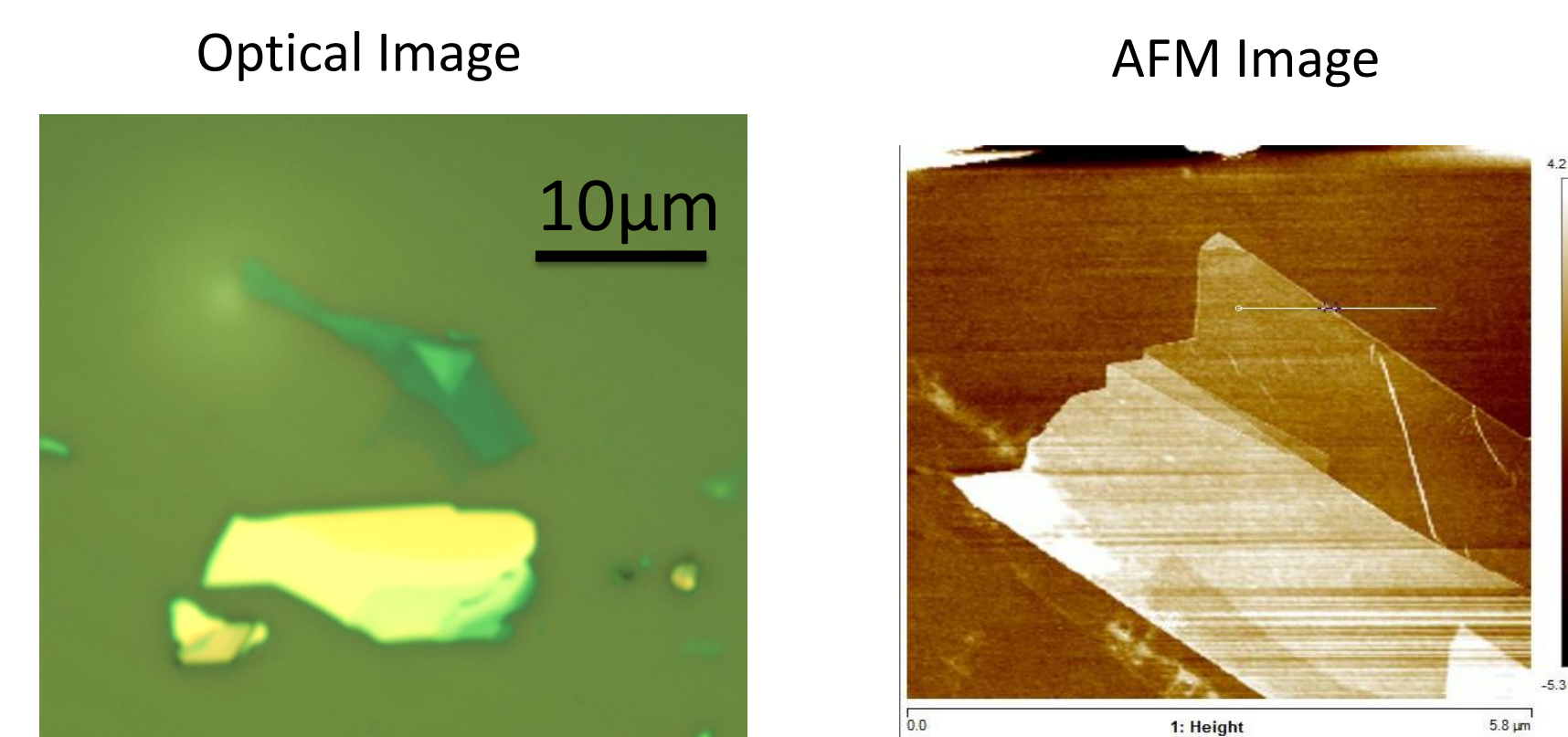
- High quality samples are produced by adhering a bulk crystal of the desired material to a piece of scotch tape. It is then repeatedly stuck together until a fine coating of the material covers the entire face of the tape. This tape is pressed and gently rubbed against a silicon oxide (SiO_2) substrate.
- Optical Microscopy is used to locate the samples on the SiO_2 substrate.

Results:

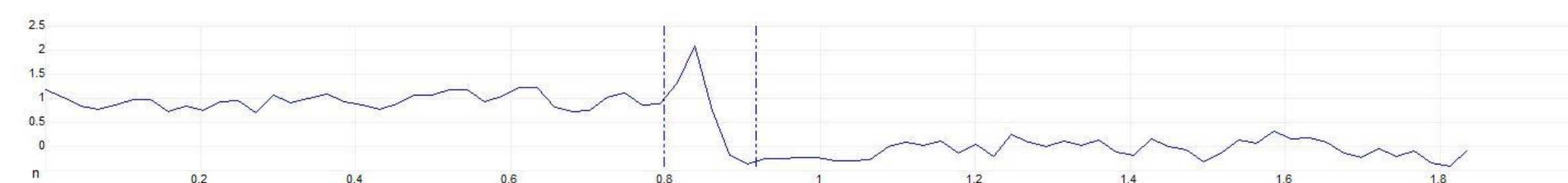


Atomic Force Microscopy (AFM)

- AFM is used to measure a number of physical properties of the sample, most notably the thickness. This is achieved by scanning a very fine tip over the sample and measuring the deflection of the cantilever as it moves across.

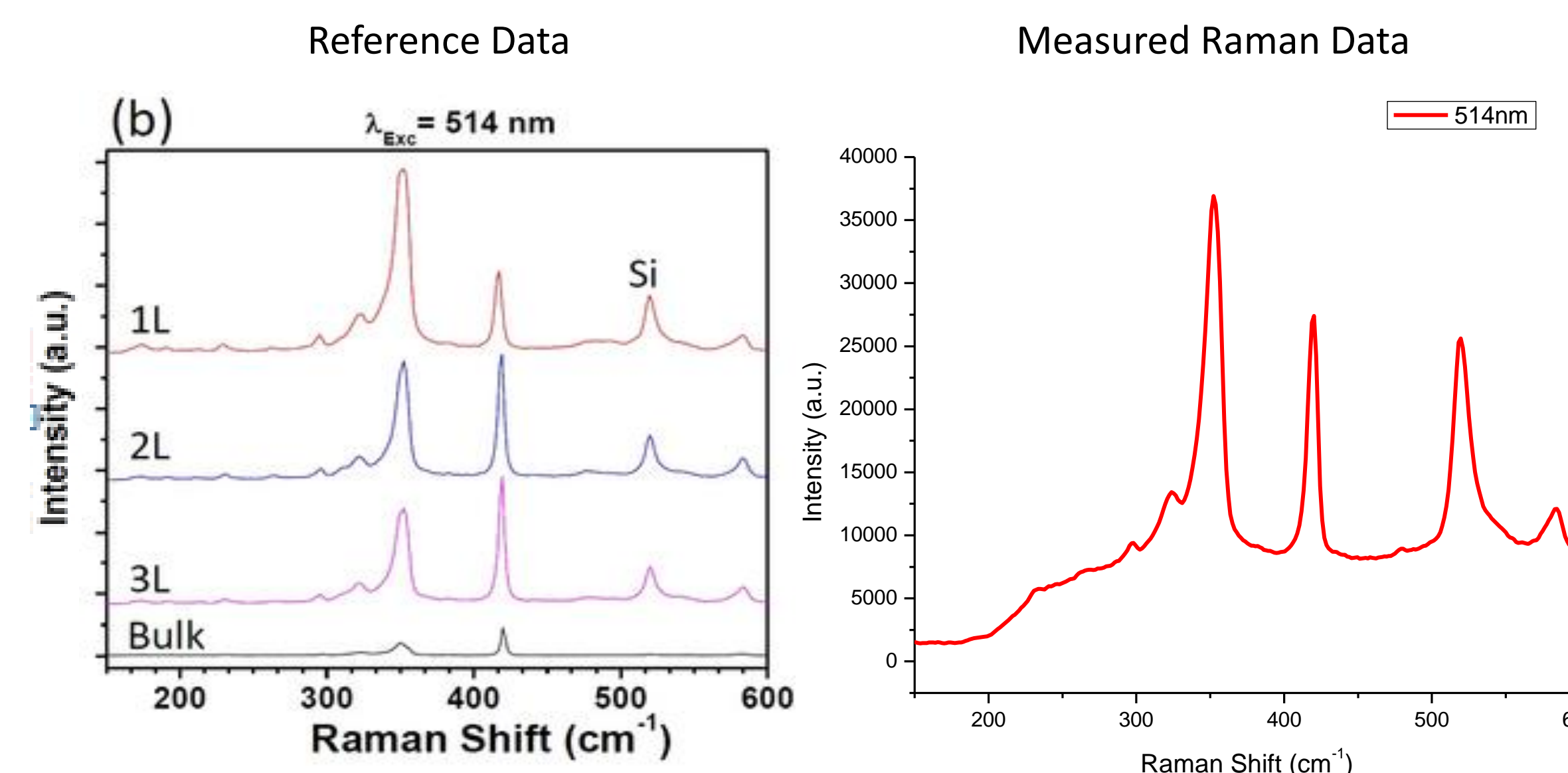


- Sample thickness is measured to be ~2.5nm (shown below)



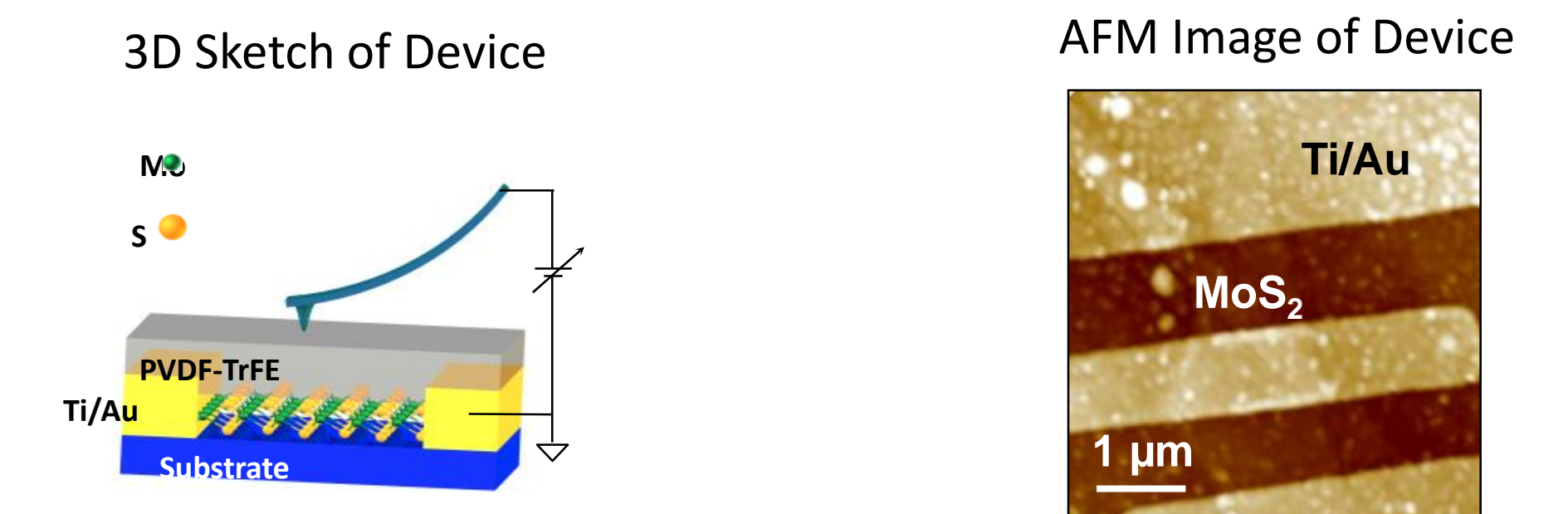
Raman Spectroscopy

- Raman Spectroscopy is carried out by using a laser to excite electrons in the target substance and measure the vibrational modes.
- Vibrational modes are unique to each material and can be used to identify both the thickness and chemical makeup of that material.



Device Fabrication and Measurements

- I designed my device using L-Edit Software, and it was fabricated by the process of electron beam lithography.



- Measurements were taken using a Keithley 2400 and Physical Property Measurement System (PPMS)

Conclusions

- I successfully learned how to exfoliate materials, design devices, and perform meaningful measurements using the Keithley 2400 and PPMS.
- With the help of my mentor, I observed the process of electron beam lithography in the NCMN cleanroom.
- The results from this research suggest interesting effects could be observed if multiple layers of varying dichalcogenides are exfoliated on top of one another and then measured with a device.

References and Acknowledgements

Xiao, et. al. Programmable Schottky Junctions Based on Ferroelectric Gated MoS_2 Transistors.

Berkdemir, et al. Identification of individual and few layers of WS_2 using Raman Spectroscopy.

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